

# TPM4-156.75 4BB

## MONOCSTALLINE SILICON SOLAR CELL

High-efficiency Mono Cells using passivated backside and local BSF Technology. Manufacturing modules with more than **290Wp (6×10)** and **345Wp (6×12)** power output becomes easier than ever.

### MECHANICAL DATA AND DESIGN

Format	156.75mm×156.75mm±0.5mm
Thickness	190μm±20μm
Front(-)	1.1 mm bus bars(silver), blue anti-reflecting coating(silicon nitride)
Back(+)	1.6 mm wide soldering pads(silver) back surface field(aluminum)

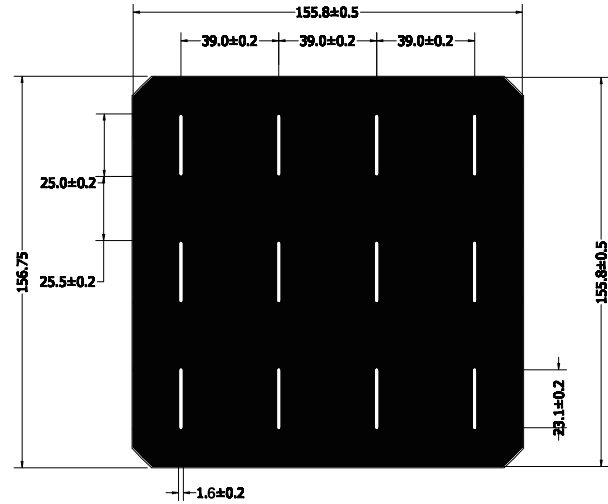
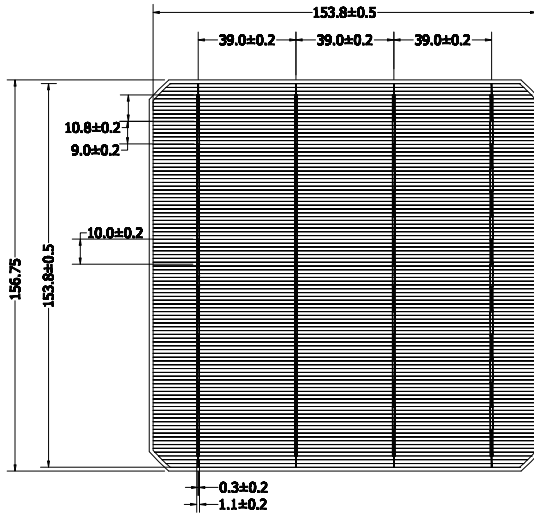
### TEMPERATURE COEFFICIENTS

TkVoltage	-0.36%/K
TkCurrent	+0.04%/K
TkPower	-0.36%/K

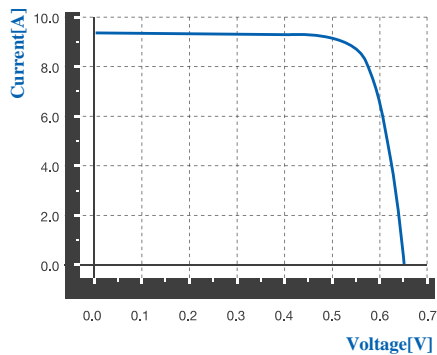
No.	Efficiency(%)	Pmpp(W)	Umpp(V)	Impp(A)	Uoc(V)	Isc(A)	FF(%)
10	20.90-21.00	5.11	0.557	9.169	0.660	9.714	79.66
09	20.80-20.90	5.08	0.556	9.142	0.659	9.695	79.51
08	20.70-20.80	5.06	0.555	9.120	0.658	9.686	79.42
07	20.60-20.70	5.04	0.554	9.104	0.657	9.676	79.32
06	20.50-20.60	5.01	0.552	9.080	0.655	9.668	79.14
05	20.40-20.50	4.99	0.551	9.061	0.654	9.658	78.98
04	20.30-20.40	4.96	0.549	9.038	0.652	9.651	78.86
03	20.20-20.30	4.94	0.548	9.023	0.650	9.646	78.77
02	20.10-20.20	4.91	0.546	8.985	0.648	9.623	78.68
01	20.00-20.10	4.89	0.545	8.972	0.648	9.611	78.54

Specifications subjects to technical changes and tests, Taipo Energy reserves the right of final interpretation.

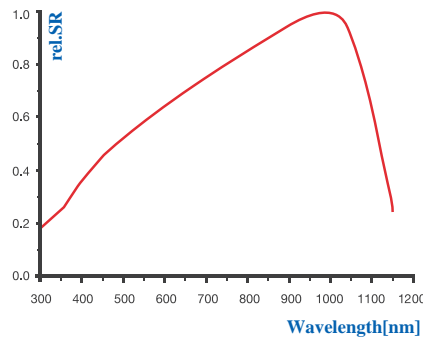
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### IV CURVE



### SPECTRAL RESPONSE



### INTENSITY DEPENDENCE

Intensity [W/m <sup>2</sup> ]	Isc*	Voc*	Pmpp
1000	1.00	1.00	1.00
900	0.90	1.00	0.90
800	0.80	0.99	0.79
500	0.50	0.97	0.49
300	0.30	0.95	0.29
200	0.20	0.93	0.19

\*Ratio of Voc(Isc) at reduced intensity to Voc(Isc) at 1000 W/m<sup>2</sup>